



Ordering Information:

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	80	A
	$I_{D@TC=75}$	60	A
	$I_{D@TC=100}$	50	A
Pulsed Drain Current	I_{DM}	190	A
Total Power Dissipation($T_C=25$)	$P_D@TC=25$	120	W
Total Power Dissipation($T_A=25$)			

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	25	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	



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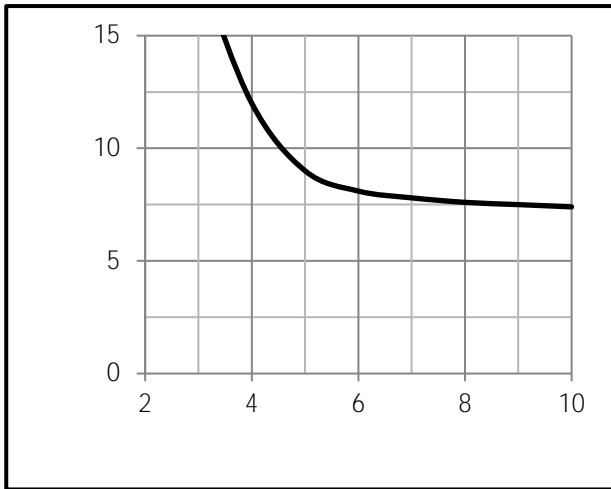


Fig.9 Switching Time Measurement Circuit

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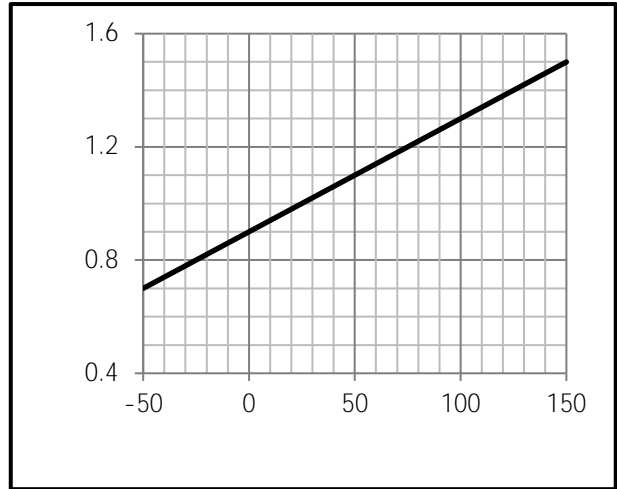


Fig.10 Gate Charge Waveform

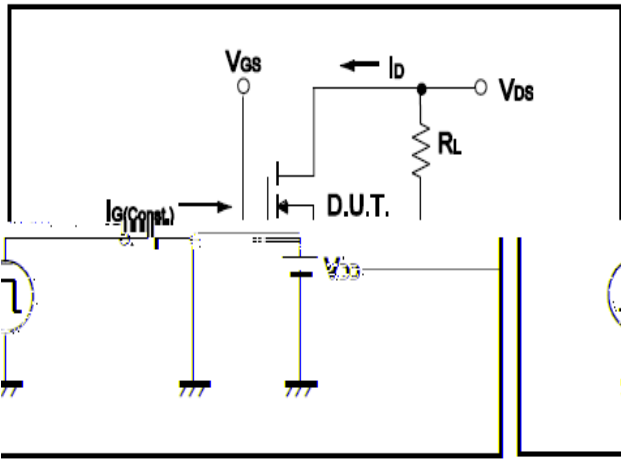


Fig.11 Switching Time Measurement Circuit

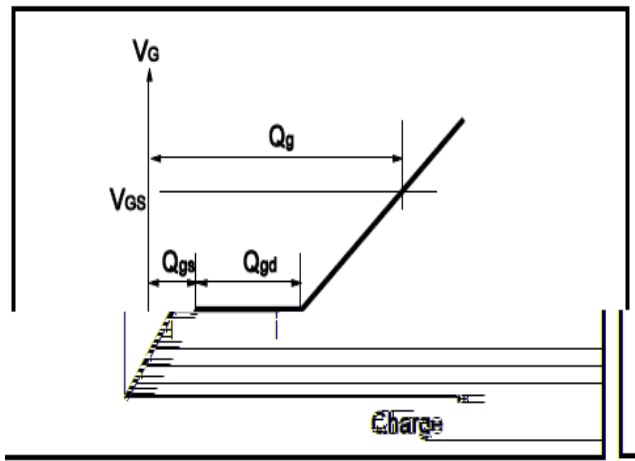
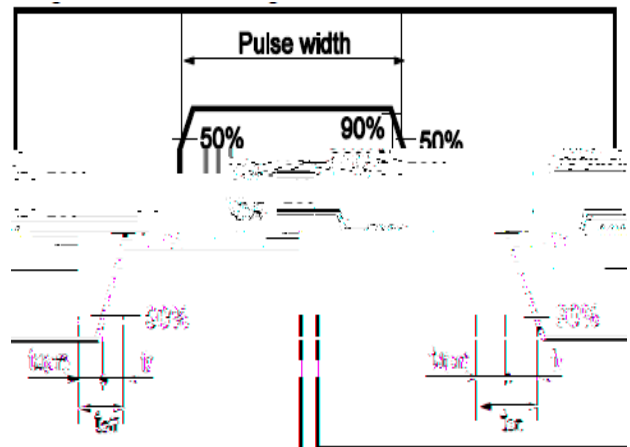
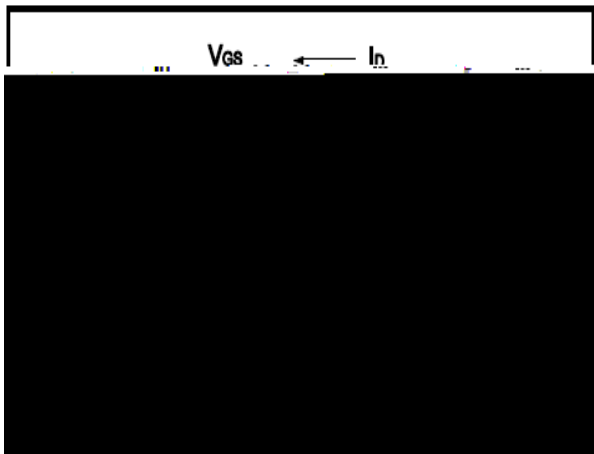


Fig.12 Gate Charge Waveform





Dimensions (TO-220)

Unit mm

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	0.		.			0 2	
	. .		2.		.		2